

Description

The SI1032R-T1-GE3 uses advanced trench technology

to provide excellent R_{DS(ON)}, low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



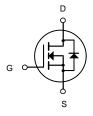
SOT-523

General Features

 $V_{DS} = 20V I_{D} = 0.8A$

 $R_{DS(ON)}$ < 250 mQ@ V_{GS} =4.5V

 $R_{DS(ON)} < 360 \text{ m}\Omega @ V_{GS} = 2.5V$



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SI1032R-T1-GE3	SOT-523	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _D s	Drain-Source Voltage	20	V
Vgs	Gate-Source Voltage	±8	V
ID	Drain Current-Continuous	0.8	А
P _D	Maximum Power Dissipation	0.15	W
Тл,Тятв	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	850	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

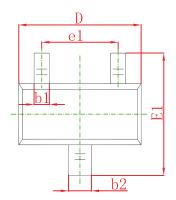
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
STATIC CHARACTERISTICE						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250µA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =20V,V _{GS} = 0V			1	μΑ
Gate-body leakage current	I _{GSS}	V _{GS} =±8V, V _{DS} = 0V			±10	μA
Gate threshold voltage (note2)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.5	0.7	1.0	V
Desir seems on the	R _{DS(on)}	V _{GS} =4.5V, I _D =0.5A		0.18	0.25	Ω
Drain-source on-resistance (note2)		V _{GS} =2.5V, I _D =0.5A		0.27	0.36	Ω
Maximum Continuous Drain to Source Diode Forward Current	Is				0.8	А
Maximum Pulsed Drain to Source Diode Forward Current	I _{SM}				1.2	Α
Diode forward voltage	V _{SD}	I _S =0.5A, V _{GS} =0V			1.2	V
DYNAMIC CHARACTERISTICS (note4)						
Input capacitance	C _{iss}			50		pF
Output capacitance	Coss	V _{DS} =16V,V _{GS} =0V, f =1MHz		7		pF
Reverse transfer capacitance	Crss	1 1141112		4.5		pF
SWITCHING CHARACTERISTICS (no	te4)					
Turn-on delay time (note3)	t _{d(on)}			2		nS
Turn-on rise time (note3)	t _r	\\ _45\\\ _40\\ B _400		32		nS
Turn-off delay time (note3)	t _{d(off)}	V_{GS} =4.5V, V_{DS} =10V, R_L =10 Ω		47		nS
Turn-off fall time (note3)	t _f			22		nS

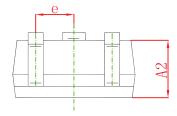
Notes:

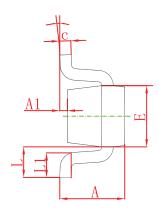
- 1. Surface mounted on FR4 board using the minimum recommended pad size.
- 2. Pulse Test : Pulse Width=300µs, Duty Cycle=2%.
- 3. Switching characteristics are independent of operating junction temperatures.
- 4. Guaranteed by design, not subject to producting.



SOT-523 Package Information

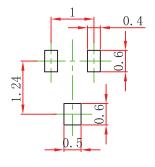






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	0.700	0.900	0.028	0.035	
A1	0.000	0.100	0.000	0.004	
A2	0.700	0.800	0.028	0.031	
b1	0.150	0.250	0.006	0.010	
b2	0.250	0.350	0.010	0.014	
С	0.100	0.200	0.004	0.008	
D	1.500	1.700	0.059	0.067	
E	0.700	0.900	0.028	0.035	
E1	1.450	1.750	0.057	0.069	
е	0.500 TYP.		0.020 TYP.		
e1	0.900	1.100	0.035	0.043	
L	0.400 REF.		0.016 REF.		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

SOT-523 Suggested Pad Layout



Note:

- 1. Controlling dimension: in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.



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